



●Applications

For terminal protection device

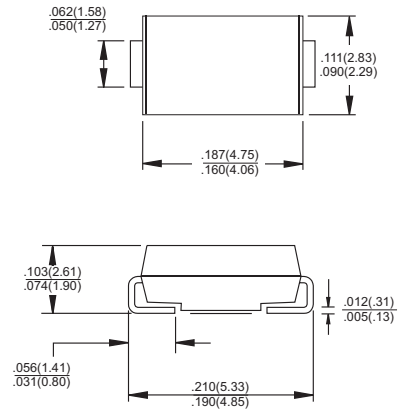
●Features

- 1) Small power mold type. (PMDS)
- 2) High reliability

●Construction

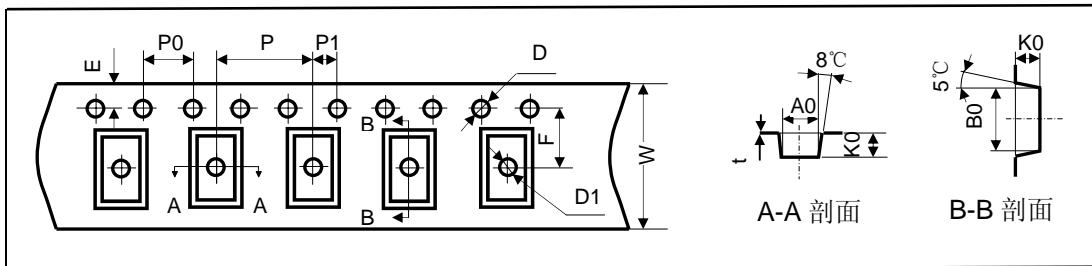
Silicon epitaxial planar

SMA/DO-214AC



Dimensions in inches and (millimeters)

●Taping specifications (Unit : mm)



产品规格 CASE TYPE (Outline)	符号 SYMBOL	DO214AC (SMA)	
口袋宽度 CARRIER WIDTH	A0	2.79±0.10 (0.110±0.004)	
口袋长度 CARRIER LENGTH	B0	5.33±0.10 (0.210±0.004)	
口袋深度 CARRIER DEPTH	K0	2.36±0.05 (0.093±0.002)	
承载带厚度 TOTAL TAPE THICKNESS	t	0.30±0.05 (0.012±0.002)	
承载带宽度 TAPE WIDTH	W	12.00±0.10 (0.472±0.004)	
口袋孔距 PUNCH HOLE PITCH	P	4.00±0.10 (0.157±0.004)	
定位孔距 SPROCKET HOLE PITCH	P0	4.00±0.10 (0.157±0.004)	
定位孔位 SPROCKET HOLE POSITION	E	1.75±0.10 (0.069±0.004)	
口袋孔位 PUNCH HOLE POSITION	F	5.50±0.05 (0.217±0.002)	
间距位置 PITCH POSITION	P1	2.00±0.05 (0.079±0.002)	
定位孔径 SPROCKET HOLE DIAMETER	D	1.55±0.05 (0.061±0.002)	
(口袋) 孔径 PUNCH HOLE DIAMETER	D1	1.50±0.10 (0.059±0.004)	

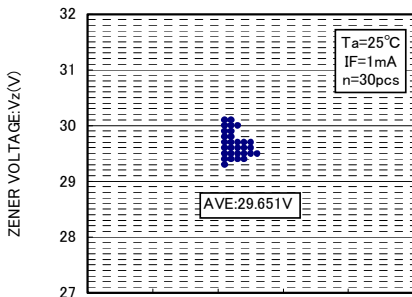
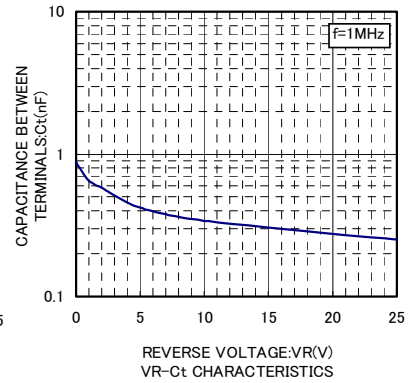
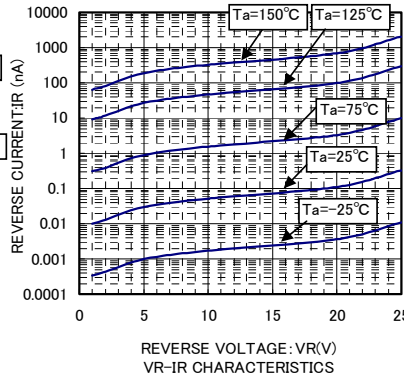
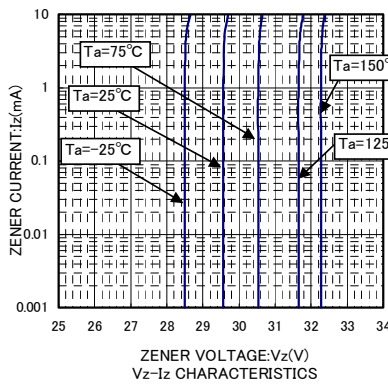


● Absolute maximum ratings (Ta=25°C)

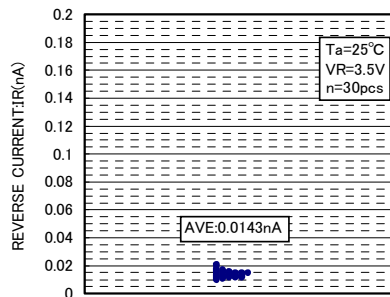
Parameter	Symbol	Limits	Unit
Peak pulse (tp=10×1000us)	Ppk	600	W
Stand off power	V <sub>RMN</sub>	25.6	V
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

● Electrical characteristics (Ta=25°C)

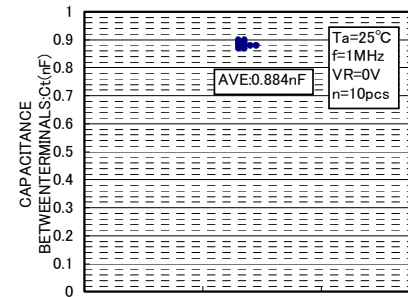
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Breakdown voltage	V <sub>BR</sub>	28.5	-	31.5	V	I <sub>R</sub> =1.0mA
Clamping voltage	V <sub>C</sub>	-	-	41.4	V	I <sub>pp</sub> =14.4A
Reverse current	I <sub>R</sub>	-	-	5	uA	V <sub>RMN</sub> =25.6V



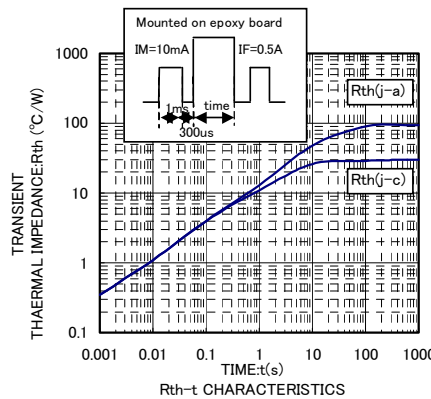
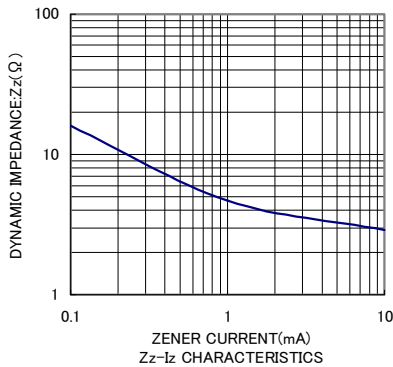
V<sub>Z</sub> DISRESION MAP



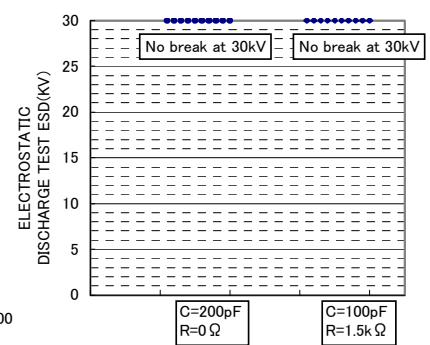
I<sub>R</sub> DISRESION MAP



C<sub>t</sub> DISRESION MAP



R<sub>th</sub>-t CHARACTERISTICS



ESD DISPERSION MAP